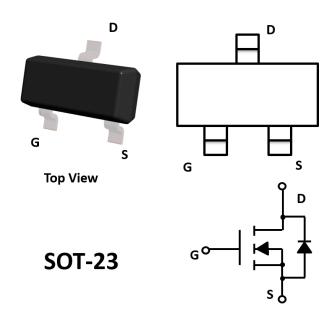




# **N-Channel Enhancement Mode Field Effect Transistor**



### **Product Summary**

 $\begin{array}{lll} \bullet \ V_{DS} & 60V \\ \bullet \ I_{D} & 340 \text{mA} \\ \bullet \ R_{DS(ON)} ( \ at \ V_{GS} = 10V) & <2.5 \text{ohm} \\ \bullet \ R_{DS(ON)} ( \ at \ V_{GS} = 4.5V) & <3.0 \text{ohm} \\ \end{array}$ 

#### **General Description**

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage

#### **Applications**

- Battery operated systems
- Solid-state relays
- Direct logic-level interface: TTL/CMOS

#### ■ **Absolute Maximum Ratings** (T<sub>A</sub>=25 °C unless otherwise noted)

	Parameter	Symbol	Limit	Unit	
Drain-source Voltage		V <sub>DS</sub>	60	V	
Gate-source Voltage		$V_{GS}$	±20	V	
Drain Current	T <sub>A</sub> =25 °C @ Steady State	I <sub>D</sub>	340	mA	
	T <sub>A</sub> =70°C @ Steady State	ID	272	IIIA	
Pulsed Drain Current <sup>A</sup>		I <sub>DM</sub>	1.5	Α	
Total Power Dissipation @ 1		P <sub>D</sub>	350	mW	
Thermal Resistance Junction	n-to-Ambient @ Steady State <sup>B</sup>	$R_{ heta JA}$	357	°C/W	
Junction and Storage Tempo	erature Range	$T_J$ , $T_STG$	-55∼+150	$^{\circ}$	

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE	
2N7002	F2	7002.	3000	30000	120000	7" reel	



# 2N7002

### ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Тур	Max	Units	
Static Parameter							
Drain-Source Breakdown Voltage BV <sub>DSS</sub> V <sub>GS</sub> =		V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	60			V	
Zero Gate Voltage Drain Current I <sub>DSS</sub>		V <sub>DS</sub> =60V,V <sub>GS</sub> =0V			1	μA	
Orto Barbal and ann Ourrent	I <sub>GSS1</sub>	$V_{GS} = \pm 20V,  V_{DS} = 0V$			±100	nA	
Gate-Body Leakage Current	I <sub>GSS2</sub>	$V_{GS} = \pm 10 V,  V_{DS} = 0 V$			±50	nA	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{D}=250\mu A$	1	1.5	2.5	V	
	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> =-300mA	0mA		2.5		
Static Drain-Source On-Resistance		V <sub>GS</sub> = 4.5V, I <sub>D</sub> =200mA		1.3	3.0	Ω	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =300mA,V <sub>GS</sub> =0V			1.2	V	
Maximum Body-Diode Continuous Current	Is				340	mA	
Dynamic Parameters							
Input Capacitance	C <sub>iss</sub>			16		pF	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V,f=1MHZ		10			
Reverse Transfer Capacitance	C <sub>rss</sub>			5.5			
Switching Parameters							
Total Gate Charge	$Q_g$	V <sub>GS</sub> =10V,V <sub>DS</sub> =30V,I <sub>D</sub> =0.3A		1.7	2.4	nC	
Turn-on Delay Time	t <sub>D(on)</sub>	$V_{GS}$ =10V, $V_{DD}$ =30V, $I_{D}$ =300mA,		5			
Turn-off Delay Time	$t_{D(off)}$	$R_{\text{GEN}}=6\Omega$		17		ns	
Reverse recovery Time	t <sub>rr</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =300mA,V <sub>R</sub> =25V, dI <sub>S</sub> /dt=- 100A/µs		30		ns	

A. Pulse Test: Pulse Width≤300us, Duty cycle ≤2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.



### ■ Typical Performance Characteristics

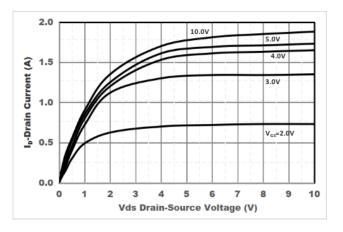


Figure 1. Output Characteristics

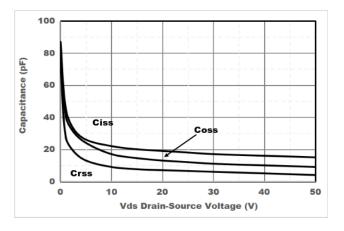


Figure 3. Capacitance Characteristics

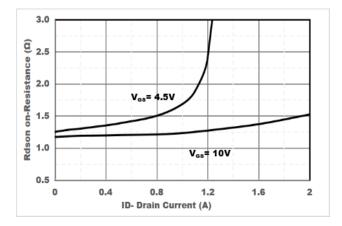


Figure 5. Drain-Source on Resistance

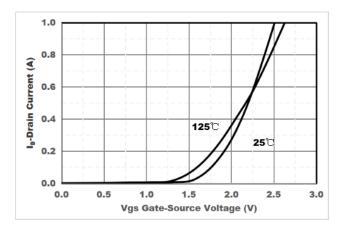


Figure 2. Transfer Characteristics

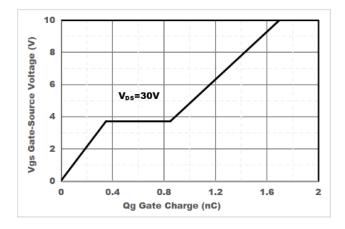


Figure 4. Gate Charge

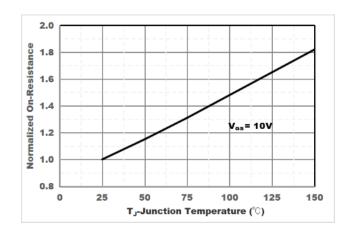
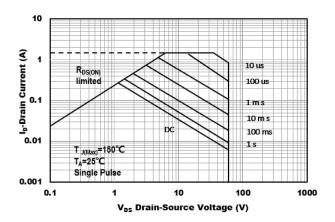


Figure 6. Drain-Source on Resistance









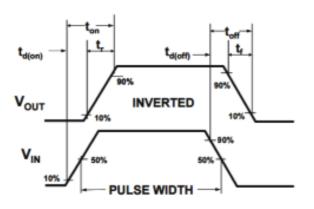
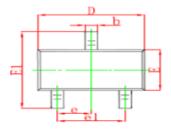
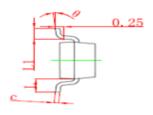


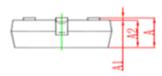
Figure8. Switching wave



### ■ SOT-23 Package information

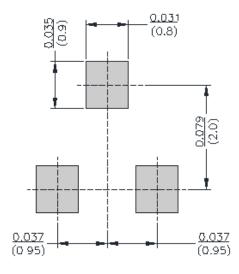






Cumbal	Dimentions	in Millimeter	Dimentions in Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950Type		0.037Type		
e1	1.800	2.000	0.071	0.079	
L	0.550REF		0.220REF		
L1	0.300	0.500	0.012	0.020	
θ	0 °	8 °	0 °	8 °	

# ■SOT-23 Suggested Pad Layout





#### 2N7002

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